



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

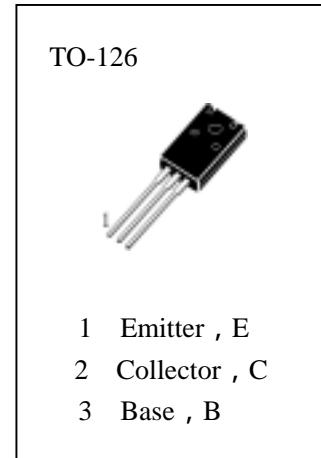
HS882

APPLICATIONS

Audio Frequency Power Amplifier , Switching Power Amplifier.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation ($T_c=25^\circ\text{C}$)	10W
P_C	Collector Dissipation ($T_A=25^\circ\text{C}$)	1W
V_{CBO}	Collector-Base Voltage.....	40V
V_{CEO}	Collector-Emitter Voltage.....	30V
V_{EBO}	Emitter-Base Voltage.....	5V
I_C	Collector Current (DC)	3A
I_B	Base Current (DC)	0.6A



Electrical Characteristics ($T_a=25^\circ\text{C}$)

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector-Base Cutoff Current			1	μA	$V_{\text{CB}}=30\text{V}, I_E=0$
I_{EBO}	Emitter- Base Cutoff Current			1	μA	$V_{\text{EB}}=5\text{V}, I_c=0$
h_{FE}	DC Current Gain	60		400		$V_{\text{CE}}=2\text{V}, I_c=1\text{A}$
$V_{\text{CE(sat)}}$	Collector- Emitter Saturation Voltage		0. 3	0. 5	V	$I_c=2\text{A}, I_B=0. 2\text{A}$
$V_{\text{BE(sat)}}$	Base -Emitter Saturation Voltage		1. 0	2. 0	V	$I_c=2\text{A}, I_B=0. 2\text{A}$
C_{ob}	Output Capacitance		45		pF	$V_{\text{CB}}=10\text{V}, I_E=0, f=1\text{MHz}$
f_T	Current Gain-Bandwidth Product		90		MHz	$V_{\text{CE}}=5\text{V}, I_E=0. 1\text{A}$

h_{FE} Classification

R	Q	P	E
60—120	100—200	160—320	200—400